Appl. No. : 10/561,802 Filed : December 22, 2005

AMENDMENTS TO THE CLAIMS

(Currently amended) A developer composition for resists, comprising an
organic quaternary ammonium base as a main component and a surfactant.

said surfactant containing an anionic surfactant represented by the following general formula (I):

$$\begin{array}{c}
R_1 \\
R_2
\end{array}$$

$$\begin{array}{c}
-0 \\
R_4
\end{array}$$

$$\begin{array}{c}
R_3 \\
R_5
\end{array}$$

wherein at least one member of R₁ and R₂ represents an alkyl or alkoxy group having 5 to 18 carbon atoms and any reminder <u>remaining</u> member represents a hydrogen atom, or an alkyl or alkoxy group having 5 to 18 carbon atoms, and at least one member of R₃, R₄ and R₅ represents a group represented by the following general formula (II):

wherein M represents a metal atom, and any reminder remaining member represent a hydrogen atom or a group represented by the above general formula (II).

- (Original) The developer composition for resists according to claim 1, wherein,
 in the general formula (II), M represents one selected from sodium, potassium and calcium,
 provided that, in the general formula (I), when two or more groups represented by the general
 formula (II) are present, M may be the same or different.
- 3. (Previously presented) A method for formation of a resist pattern, comprising applying a resist composition on a substrate to form a resist layer, prebaking the resist layer, selectively exposing the prebaked resist layer to light, and alkali-developing the exposed resist layer with the developer composition for resists according to claim 1 to form a resist pattern.
- 4. (Previously presented) A method for formation of a resist pattern, comprising applying a resist composition on a substrate to form a resist layer, prebaking the resist layer, selectively exposing the prebaked resist layer to light, and alkali-developing the exposed resist layer with the developer composition for resists according to claim 2 to form a resist pattern.